

1. Scope :

This specification applies to silicon PIN photodiode chips,  
Device No. PD-1030.

2. Structure :

- 2-1. Planar type : PIN.
- 2-2. Electrodes :  
Top side(Anode 1 & Anode 2 ) : Aluminum alloy.  
Back side ( Cathode ) : Gold.

3. Size :

- 3-1. Chip size (including scribe lane) : 80mils x 30 mils (3.18 mm x 1.18mm ).
- 3-2. Chip thickness : 7.5± 0.39 mils ( 0.200 ± 0.010 mm).
- 3-3. Active area : 143.3 mils x 51.1 mils (3.64 mm x 1.3 mm ).
- 3-4. Bonding pad (Anode) : 5.1 ± 0.39 mils ( 0.13 ± 0.010 mm ) Diameter
- 3-5. Pattern drawing : Refer to the attached drawing..

4. Electrical characteristics (Ta = 25 °C)

| Parameter                   | Symbol | Condition                                    | Min. | Typ. | Max. | Unit |
|-----------------------------|--------|----------------------------------------------|------|------|------|------|
| * Reverse dark current      | Id     | VR=20V<br>Ee=0mW/cm <sup>2</sup>             |      |      | 10   | nA   |
| * Reverse breakdown voltage | V(BR)R | IR=100uA<br>Ee=0mW/cm <sup>2</sup>           | 35   |      |      | V    |
| Reverse light current       | IL     | VR =1V<br>λp=940nm<br>Ee=1mW/cm <sup>2</sup> |      | 16   |      | μA   |
| Radiant Sensitivity         | Sλ     | λp=940nm                                     |      | 0.55 |      | A/W  |
| Spectral Response           | SR     |                                              | 430  |      | 1100 | nm   |

Based on 100% probing

